



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive applications.

Features

- $BV_{CEO} > -45V$
- $I_C = -100mA$ Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: NK-BC847BTQ

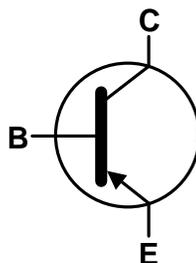
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 
- Weight: 0.002 grams (Approximate)

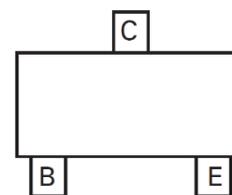
SOT523



Top View



Device Symbol



Pin-Out Top View

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-100	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	150	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

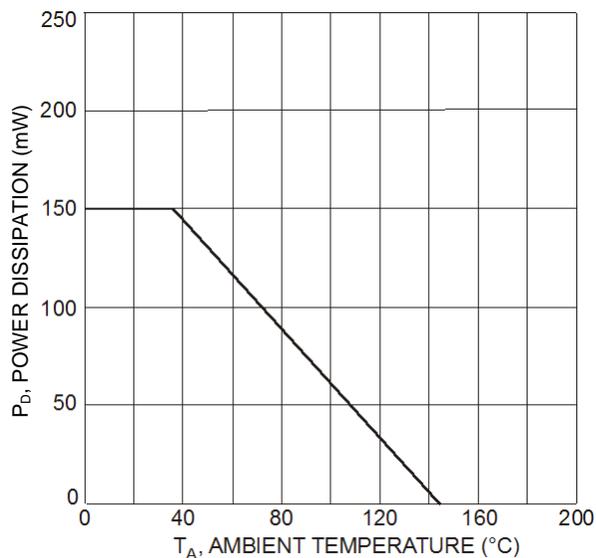
Thermal Characteristics and Derating Information


Fig. 1, Power Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	I _C = -10μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -10μA
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h _{FE}	220	290	475	—	V _{CE} = -5.0V, I _C = -2.0mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	-300 -650	mV	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-700 -900	—	mV	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5.0mA
Base-Emitter Voltage	V _{BE(ON)}	-600	—	-750 -820	mV	V _{CE} = -5.0V, I _C = -2.0mA V _{CE} = -5.0V, I _C = -10mA
Collector-Emitter Cutoff Current	I _{CBO}	—	—	-15 -4.0	nA μA	V _{CB} = -30V V _{CB} = -30V, T _A = +150°C
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{OBO}	—	—	4.5	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	100	—	—	MHz	V _{CE} = -5.0V, I _C = -10mA, f = 100MHz
Noise Figure	N _F	—	—	10	dB	I _C = -0.2mA, V _{CE} = -5.0V, R _S = 2.0kΩ, f = 1.0KHz, BW = 200Hz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

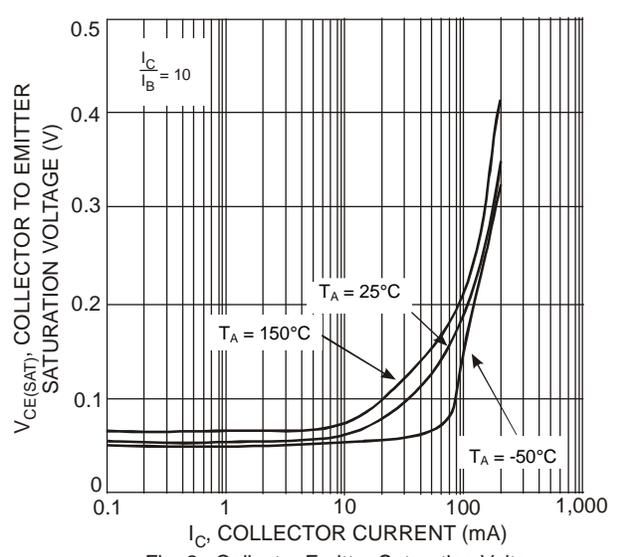


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

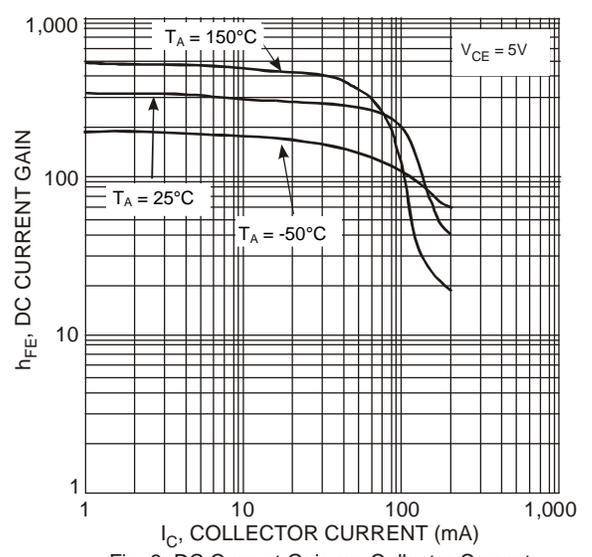


Fig. 3, DC Current Gain vs. Collector Current

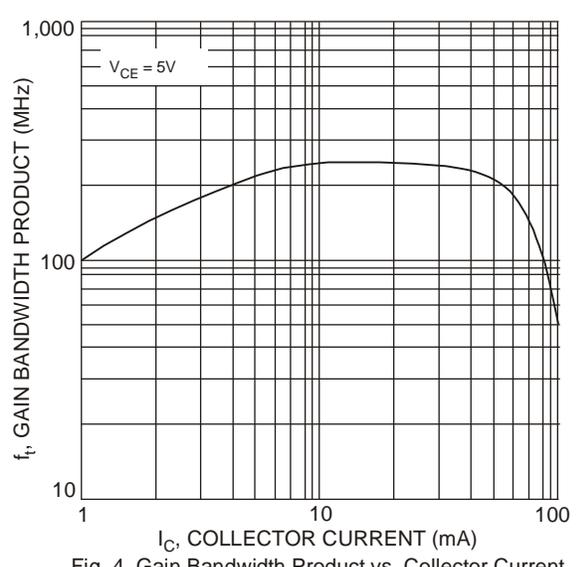
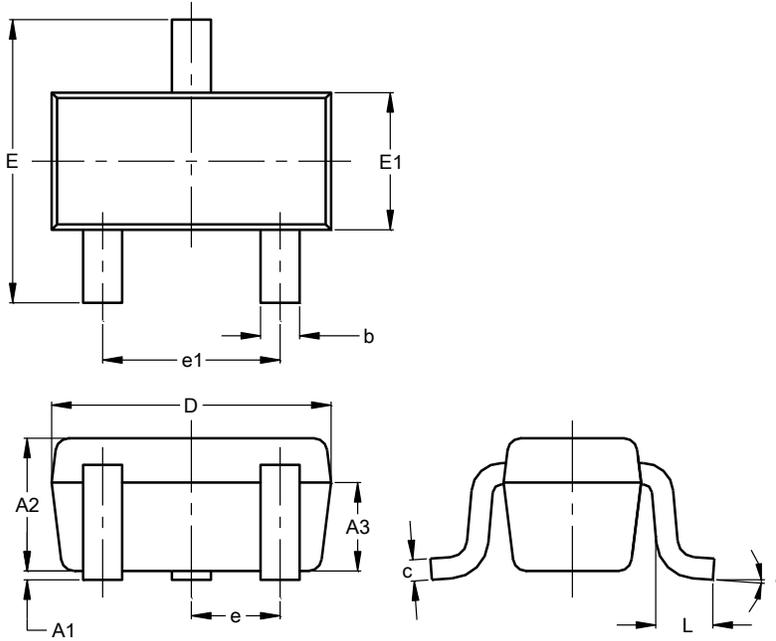


Fig. 4, Gain Bandwidth Product vs. Collector Current

Package Outline Dimensions

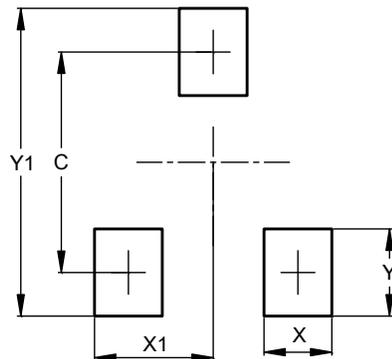
SOT523



SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

Suggested Pad Layout

SOT523



Dimensions	Value
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80